

FileViewEditToolsWindowHelp

Active

L1: (155) (((cell memory) near2 ((area region section portion D

L2: (100531) cmos

L3: (94) 1 and 2

L4: (22678) pmos with nmos

L5: (70) 3 and 4

L6: (110) (257/214) CCLS

Failed

Saved

(1) 08/848877

(1736) "KONINKLLIKE PHILIPS".as.

(2) 10/253779

(1) 10/234501

(37717) n-well pmos

(43184) p-well nmos

(1978052) peripher\$2 logic

(2357117) cell memory

(182171) (peripher\$2 logic D) with (cell memory)

(3810307) region area

(82488) (cell memory) adj2 (region area)

(7362802) (area region section portion)

(215405) (cell memory) near2 ((area region section portion D)

(270282) (peripher\$2 logic D) near2 ((area region section portion D)

(809846) polysilicon poly adj silicon silicon

(3102552) metal

BrowseQueueClear

DBs:USPAT,US PGPUB,EPO,JPO,DERVENT,ISOM,TDD

Default operator:OR

P Plurals

P Highlight all hit terms initially

10/253779

Feb. 2 2004

A-BIS ItemA-BIS ItemImageFileImage

	U	+	Investor	Document#	Issue#	P	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc.	P
1	<input type="checkbox"/>	<input type="checkbox"/>	Cho, Heung J	US 2003008	20030	2	CMOS of semiconductor device and method f 257/369;257/E21.63				<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200300
2	<input type="checkbox"/>	<input type="checkbox"/>	Cho, Heung J	US 6642132	20031	2	Cmos of semiconductor device and method f 438/582;257/315				<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 664213

Ready

Ready